

### **Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application.

### **Listing of Claims:**

1. (Previously Presented) A surface emitting semiconductor laser chip, comprising:  
a semiconductor body having a radiation exit face,  
a crystal structure having principal crystal directions extending along a lateral direction of the radiation exit face, and  
side faces laterally delimiting said semiconductor body, at least one of said side faces disposed obliquely with respect to said principal crystal directions and perpendicularly with respect to said radiation exit face.
2. (Original) The semiconductor laser chip according to claim 1, wherein said semiconductor body has a cross section selected from the group of square cross sections and rectangular cross sections disposed parallel to said radiation exit face.
3. (Previously Presented) The semiconductor laser chip according to claim 1, wherein at least one of said principal crystal directions extends parallel to said radiation exit face, and at least one of said side faces forms an angle of between 40° and 50° with said at least one principal crystal direction.
4. (Original) The semiconductor laser chip according to claim 1, wherein said semiconductor body contains a substrate having, at least partly, a crystal structure.

5. (Original) The semiconductor laser chip according to claim 4, wherein said semiconductor body contains a III-V compound semiconductor.

6. (Original) The semiconductor laser chip according to claim 1, wherein the semiconductor laser chip is a VCSEL.

7. (Original) The semiconductor laser chip according to claim 3, wherein said angle is  $45^\circ$ .

8. (Original) The semiconductor laser chip according to claim 5, wherein said III-V compound semiconductor is selected from the group consisting of GaAs, AlGaAs, and a nitride compound semiconductor.

9. (Previously presented) The semiconductor laser chip according to claim 3, wherein said at least one principal crystal direction is a [100] direction.

10 - 15 (Canceled)

16. (New) The semiconductor laser chip according to claim 1, wherein the radiation exit face is a polygon having an even number of sides, wherein the side faces are disposed obliquely with respect to the principal crystal direction and perpendicularly with respect to said radiation exit face.

17. (new) The semiconductor laser chip according to claim 16, wherein the polygon is a rectangle.